

BC546, B
BC547, A, B, C
BC548, A, B, C

TRANSISTOR (NPN)

FEATURES

Power dissipation

P_{CM} : 0.625 W ($T_{amb}=25^{\circ}C$)

Collector current

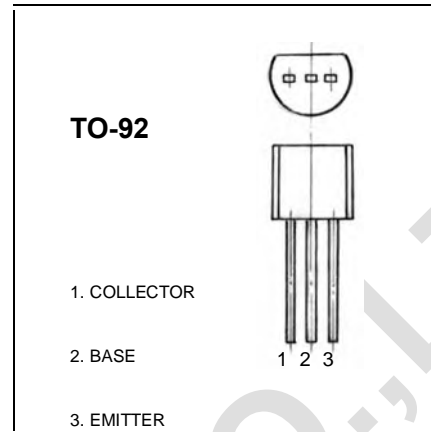
I_{CM} : 0.1 A

Collector-base voltage

V_{CBO} :	BC546	80	V
	BC547	50	V
	BC548	30	V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	V_{CBO}	$I_C = 100\mu A, I_E = 0$	80		V
			50		
			30		
Collector-emitter breakdown voltage	V_{CEO}	$I_C = 1mA, I_B = 0$	65		V
			45		
			30		
Emitter-base breakdown voltage	V_{EBO}	$I_E = 10\mu A, I_C = 0$	6		V
Collector cut-off current	I_{CBO}	$V_{CB} = 70V, I_E = 0$		0.1	μA
		$V_{CB} = 50V, I_E = 0$			
		$V_{CB} = 30V, I_E = 0$			
Collector cut-off current	I_{CEO}	$V_{CE} = 60V, I_B = 0$		0.1	μA
		$V_{CE} = 45V, I_B = 0$			
		$V_{CE} = 30V, I_B = 0$			
Emitter cut-off current	I_{EBO}	$V_{EB} = 5V, I_C = 0$		0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = 5V, I_C = 2mA$	110	450	
			110	800	
			110	800	
			110	220	
			200	450	
			420	800	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 100mA, I_B = 5mA$		0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 100mA, I_B = 5mA$		1	V
Transition frequency	f_T	$V_{CE} = 5V, I_C = 10mA$ $f = 100MHz$	150		MHz